High Speed CMOS Logic – 54HC139

Dual 1-of-4 Decoder / Demultiplexer in bare die form

Rev 1.1
21/07/20

Description

The 54HC139 is fabricated using a 2.5µm 5V CMOS process and has the same high speed performance of LSTTL combined with CMOS low power consumption. This device consists of x2 independent 1–of–4 decoders, each decoding a 2 bit address to 1–of–4 active–low outputs. Active–low Selects facilitate the demultiplexing and cascading functions. The demultiplexing function is executed by using the Address inputs to select the desired device output and utilizing the Select as a data input.

Features:

- Output Drive Capability: 10 LSTTL Loads
- Low Input Current: 1µA
- Outputs directly interface CMOS, NMOS and TTL
- Operating Voltage Range: 2V to 6V
- CMOS High Noise Immunity
- Function compatible with 54LS139
- Full Military Temperature Range.

Ordering Information

The following part suffixes apply:

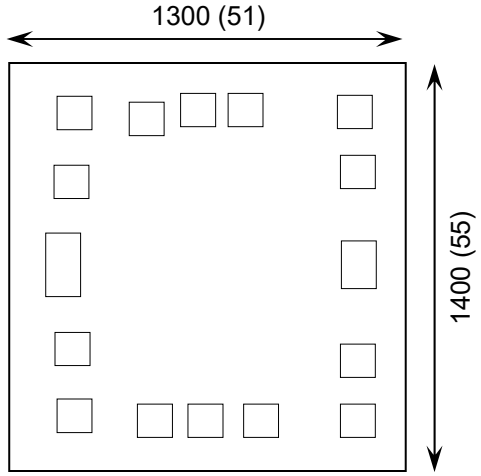
- No suffix - MIL-STD-883 /2010B Visual Inspection
- "**H**" - MIL-STD-883 /2010B Visual Inspection
  + MIL-PRF-38534 Class H LAT
- "**K**" - MIL-STD-883 /2010A Visual Inspection (Space)
  + MIL-PRF-38534 Class K LAT

LAT = Lot Acceptance Test.

For further information on LAT process flows see below.

www.siliconsupplies.com\quality\bare-die-lot-qualification

Die Dimensions in µm (mils)



Supply Formats:

- Default – Die in Waffle Pack (400 per tray capacity)
- Sawn Wafer on Tape – On request
- Unsawn Wafer – On request
- Die Thickness <> 350µm(14 Mils) – On request
- Assembled into Ceramic Package – On request

Mechanical Specification

Die Size (Unsawn)	1300 x 1400 51 x 55	µm mils
Minimum Bond Pad Size	106 x 106 4.17 x 4.17	µm mils
Die Thickness	350 (±20) 13.78 (±0.79)	µm mils
Top Metal Composition	Al 1%Si 1.1µm	
Back Metal Composition	N/A – Bare Si	

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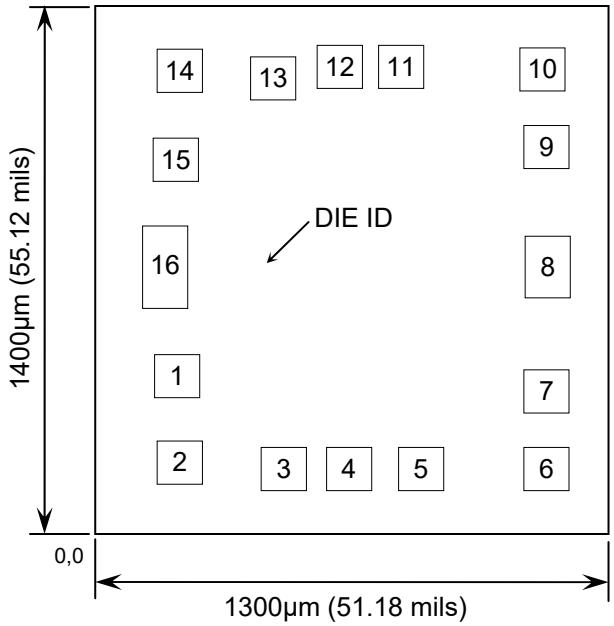
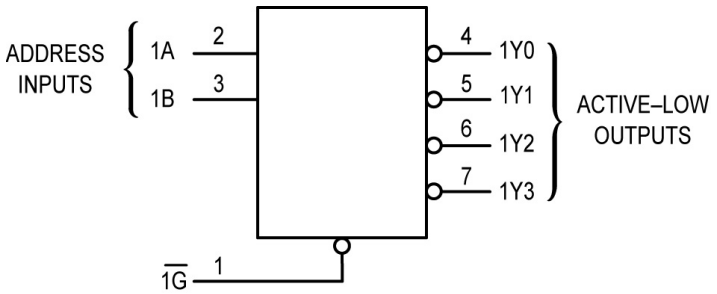
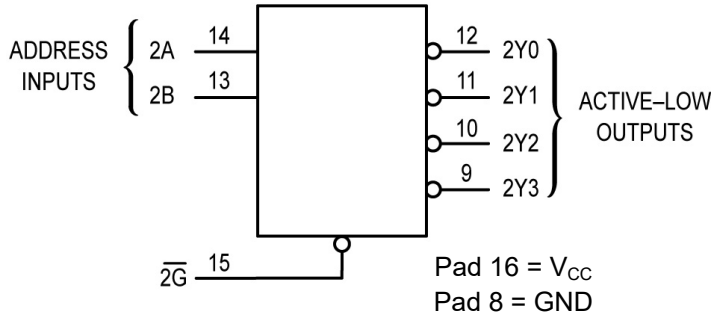
Pad Layout and Functions



PAD	FUNCTION	COORDINATES (mm)	
		X	Y
1	$\overline{1G}$	0.152	0.366
2	1A	0.162	0.132
3	1B	0.422	0.122
4	1Y0	0.59	0.122
5	1Y1	0.772	0.122
6	1Y2	1.088	0.122
7	1Y3	1.088	0.333
8	GND	1.088	0.619
9	2Y3	1.088	0.972
10	2Y2	1.078	1.173
11	2Y1	0.722	1.183
12	2Y0	0.566	1.183
13	2B	0.396	1.153
14	2A	0.162	1.173
15	$\overline{2G}$	0.152	0.938
16	V_{CC}	0.122	0.591
CONNECT CHIP BACK TO V_{CC} OR FLOAT			

Logic Diagram





Pad 16 = V_{CC}
Pad 8 = GND

Truth Table

INPUTS			OUTPUTS			
$\overline{G}$	B	A	Y0	Y1	Y2	Y3
H	X	X	H	H	H	H
L	L	L	L	H	H	H
L	L	H	H	L	H	H
L	H	L	H	H	L	H
L	H	H	H	H	H	L

X = don't care

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Absolute Maximum Ratings[1]

PARAMETER	SYMBOL	VALUE	UNIT
DC Supply Voltage (Referenced to GND)	V_{CC}	-0.5 to +7.0	V
DC Input Voltage (Referenced to GND)	V_{IN}	-1.5 to V_{CC} +1.5	V
DC Output Voltage (Referenced to GND)	V_{OUT}	-0.5 to V_{CC} +0.5	V
DC Input Current, per pin	I_{IN}	±20	mA
DC Output Current, per pin	I_{OUT}	±25	mA
DC V_{CC} or GND Current, per pin	I_{CC}	±50	mA
Power Dissipation in Still Air[2]	P_D	750	mW
Storage Temperature Range	T_{STG}	-65 to 150	°C

1. Operation above the absolute maximum rating may cause device failure. Operation at the absolute maximum ratings, for extended periods, may reduce device reliability. **2.** Measured in plastic DIP package, results in die form are dependent on die attach and assembly method.

Recommended Operating Conditions[3] (Voltages referenced to GND)

PARAMETER		SYMBOL	MIN	MAX	UNITS
DC Supply Voltage		V_{CC}	2	6	V
DC Input or Output Voltage		V_{IN} ,V_{OUT}	0	V_{CC}	V
Operating Temperature Range		T_J	-55	+125	°C
Input Rise and Fall Time	V_{CC} = 2.0V	t_r, t_f	0	1000	ns
	V_{CC} = 4.5V		0	500	
	V_{CC} = 6.0V		0	400	

3. This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation, V_{IN} and V_{OUT} should be constrained to the range GND ≤ (V_{IN} or V_{OUT}) ≤ V_{CC}. Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

DC Electrical Characteristics (Voltages Referenced to GND)

PARAMETER	SYMBOL	V_{CC}	CONDITIONS	LIMITS			UNITS
				25°C	85°C	FULL RANGE[4]	
Minimum High-Level Input Voltage	V_{IH}	2.0V	V_{OUT} = 0.1V or V_{CC} -0.1V $\lvert I_{OUT} \rvert$ ≤ 20μA	1.5	1.5	1.5	V
		4.5V		3.15	3.15	3.15	
		6.0V		4.2	4.2	4.2	
Maximum Low-Level Input Voltage	V_{IL}	2.0V	V_{OUT} = 0.1V or V_{CC} -0.1V $\lvert I_{OUT} \rvert$ ≤ 20μA	0.5	0.5	0.5	V
		4.5V		1.35	1.35	1.35	
		6.0V		1.8	1.8	1.8	

4. -55°C ≤ T_J ≤ +125°C

DC Electrical Characteristics (Voltages Referenced to GND)

PARAMETER	SYMBOL	V_{CC}	CONDITIONS	LIMITS			UNITS
				25°C	85°C	FULL RANGE[4]	
Minimum High-Level Output Voltage	V_{OH}	2.0V	$V_{IN} = V_{IH}$ or V_{IL} $\lvert I_{OUT} \rvert \leq 20\mu A$	1.9	1.9	1.9	V
		4.5V		4.4	4.4	4.4	
		6.0V		5.9	5.9	5.9	
		4.5V	$V_{IN} = V_{IH}$ or V_{IL} $\lvert I_{OUT} \rvert \leq 4.0mA$	3.98	3.84	3.70	
		6.0V	$V_{IN} = V_{IH}$ or V_{IL} $\lvert I_{OUT} \rvert \leq 5.2mA$	5.48	5.34	5.20	
Maximum Low-Level Output Voltage	V_{OL}	2.0V	$V_{IN} = V_{IH}$ or V_{IL} $\lvert I_{OUT} \rvert \leq 20\mu A$	0.1	0.1	0.1	V
		4.5V		0.1	0.1	0.1	
		6.0V		0.1	0.1	0.1	
		4.5V	$V_{IN} = V_{IH}$ or V_{IL} $\lvert I_{OUT} \rvert \leq 4.0mA$	0.26	0.33	0.40	
		6.0V	$V_{IN} = V_{IH}$ or V_{IL} $\lvert I_{OUT} \rvert \leq 5.2mA$	0.26	0.33	0.40	
Maximum Input Leakage Current	I_{IN}	6.0V	$V_{IN} = V_{CC}$ or GND	±0.1	±1.0	±1.0	µA
Maximum Quiescent Supply Current	I_{CC}	6.0V	$V_{IN} = V_{CC}$ or GND $I_{OUT} = 0\mu A$	4	40	160	µA

AC Electrical Characteristics[5]

PARAMETER	SYMBOL	V_{CC}	CONDITIONS	LIMITS			UNITS
				25°C	85°C	FULL RANGE[4]	
Maximum Propagation Delay, Select to Output Y (Figure 1, 3)	t_{PLH}, t_{PHL}	2.0V	$C_L = 50pF$, $t_r = t_f = 6ns$	115	145	175	ns
		4.5V		23	29	35	
		6.0V		20	25	30	
Maximum Propagation Delay, Input A to Output Y (Figure 2,3)	t_{PLH}, t_{PHL}	2.0V	$C_L = 50pF$, $t_r = t_f = 6ns$	115	145	175	ns
		4.5V		23	29	35	
		6.0V		20	25	30	
Maximum Output Transition Time, Any Output (Figure 1,3)	t_{TLH}, t_{THL}	2.0V	$C_L = 50pF$, $t_r = t_f = 6ns$	75	95	110	ns
		4.5V		15	19	22	
		6.0V		13	16	19	
Maximum Input Capacitance	C_{IN}	-	-	10	10	10	pF
Power Dissipation Capacitance (Per Decoder)[7]	C_{PD}	-	$T_J = 25°C$, $V_{CC} = 5.0V$	TYPICAL			
				55			pF

6. Not production tested in die form, characterized by chip design and tested in package.
7. Used to determine the no-load dynamic power consumption: $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$.

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Pad Description

ADDRESS INPUTS
1A, 1B, 2A, 2B
(Pads 2, 3, 14, 13)
When the respective 1–of–4 decoder is enabled these inputs determine which of its four active–low outputs is selected.

CONTROL INPUTS
$\overline{1G}$, $\overline{2G}$
(Pads 1, 15)
Active–low select inputs. For a low level on this input, the outputs for that particular decoder follow the Address inputs. A high level on this input forces all outputs to a high level.

OUTPUTS
1Y0, 1Y1, 1Y2, 1Y3, 2Y0, 2Y1, 2Y2, 2Y3
(Pads 4-7, 12, 11, 10, 9)
Active–low outputs. These outputs assume a low level when addressed and the appropriate Select input is active. These outputs remain high when not addressed or the appropriate Select input is inactive.

Switching Waveforms

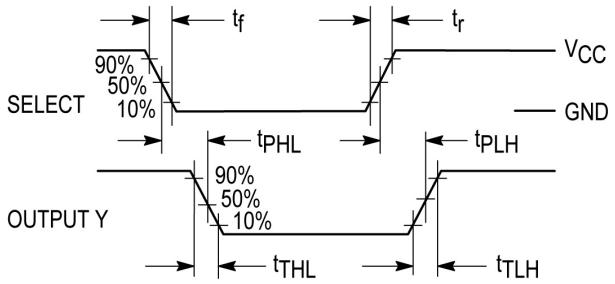


Figure 1

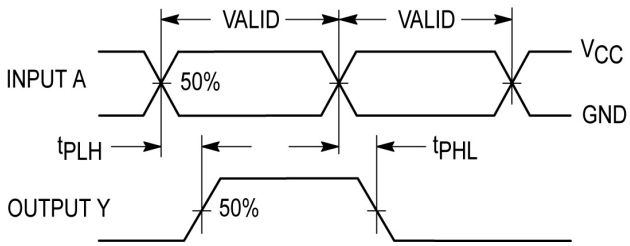
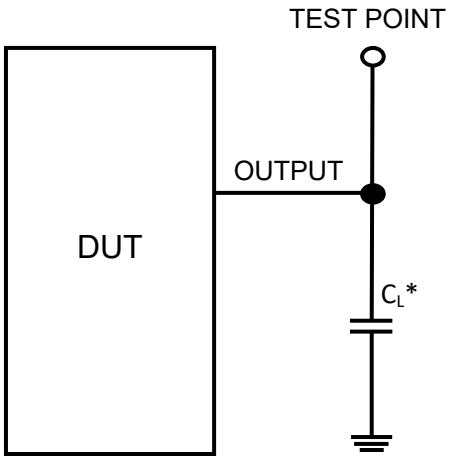


Figure 2

Test Circuit



* Includes all probe and jig capacitance

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